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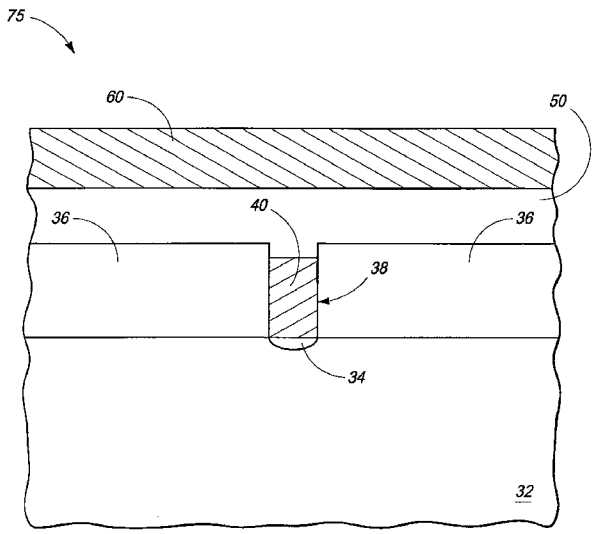


Fig. 5

(57) Abstract: A method of depositing an antimony-comprising phase change material onto a substrate includes providing a reducing agent and vaporized $Sb(OR)_3$ to a substrate, where R is alkyl, and forming there-from antimony-comprising phase change material on the substrate. The phase change material has no greater than 10 atomic percent oxygen, and includes another metal in addition to antimony.

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